TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74HC259AP, TC74HC259AF, TC74HC259AFN

#### 8 - BIT ADDRESSABLE LATCH

The TC74HC259A is a high speed CMOS ADDRESSABLE LATCH fabricated with silicon gate C2MOS technology.

It achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

The respective bits are controlled by address inputs A, B, and C. When  $\overline{CLEAR}$  input is held high and enable input G is held low, the data is written into the bit selected by address inputs, the other bit hold their previous conditions.

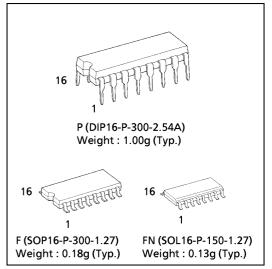
When both  $\overline{\text{CLEAR}}$  and  $\overline{\text{G}}$  held high, writing of all bits is inhibited regardless of adress inputs, and their previous condition are held. When  $\overline{\text{CLEAR}}$  is held low and  $\overline{\text{G}}$  is held high, all bits are resent to low regardless of the other inputs. When both of  $\overline{\text{CLEAR}}$  and  $\overline{\text{G}}$  held low, all bits whichi isn't selected by adress inputs are resent to low.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

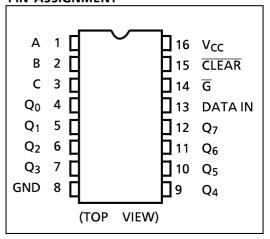
#### **FEATURES:**

- High Speed······ $t_{pd} = 15ns(typ.)$  at  $V_{CC} = 5V$
- Low Power Dissipation ············ $I_{CC} = 4\mu A(Max.)$  at Ta = 25°C
- High Noise Immunity  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Output Drive Capability ..... 10 LSTTL Loads
- Symmetrical Output Impedance… | I<sub>OH</sub> | = I<sub>OL</sub> = 4mA(Min.)
- Balanced Propagation Delays ····· t<sub>pLH</sub> ≃ t<sub>pHL</sub>
- Wide Operating Voltage Range····  $V_{CC}$  (opr.) =  $2V \sim 6V$
- Pin and Function Compatible with 74LS259

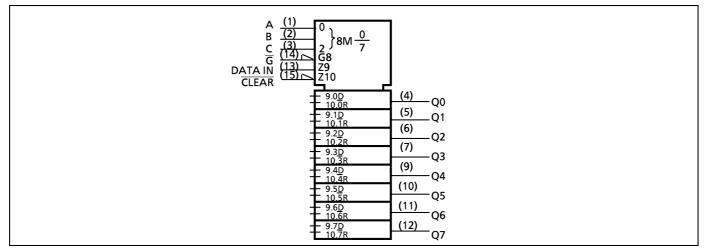
(Note) The JEDEC SOP (FN) is not available in Japan.



#### **PIN ASSIGNMENT**



#### **IEC LOGIC SYMBOL**



1

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#### TRUTH TABLE

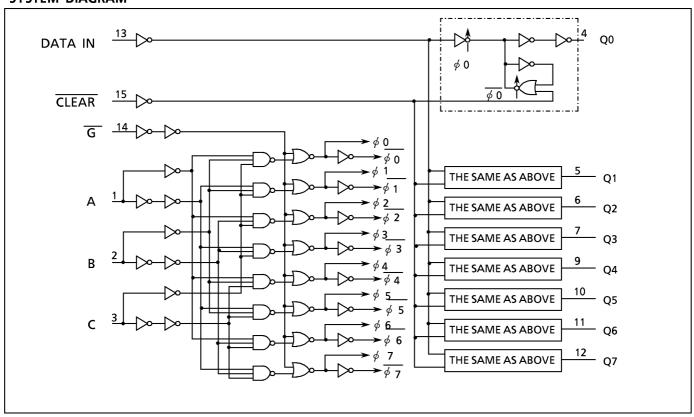
INPUTS		OUTPUT OF ADDRESSED	EACH OTHER	FUNCTION				
CLEAR	G	LATCH	OUTPUT	, sitemon				
П	L	D	QiO	ADDRESSABLE LATCH				
Н	Н	QiO	QiO QiO	MEMORY				
L	L	D	L	8—LINE DEMULTRIPLEXER				
L	Н	L	L	CLEAR ALL BITS TO "L"				

SEI	LECT INPU	JTS	LATCH				
С	В	Α	ADDRESSED				
L	L	L	Q0				
L	L	Н	Q1				
L	Н	L	Q2				
L	Н	Н	Q3				
Н	L	L	Q4				
Н	L	Н	Q4 Q5 Q6				
Н	Н	L	Q6				
Н	Н	Н	Q7				

D: The level at the data input.

OiO: The level before the indicared steady—state input conditions were established (i = 0, 1, ...7)

#### SYSTEM DIAGRAM



## **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>CC</sub>	-0.5~7.0	V
DC Input Voltage	V <sub>IN</sub>	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V <sub>OUT</sub>	−0.5~V <sub>CC</sub> + 0.5	V
Input Diode Current	I <sub>IK</sub>	± 20	mA
Output Diode Current	I <sub>OK</sub>	± 20	mA
DC Output Current	I <sub>OUT</sub>	± 25	mA
DC V <sub>CC</sub> / Ground Current	I <sub>cc</sub>	± 50	mA
Power Dissipation	P <sub>D</sub>	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T <sub>stg</sub>	<b>−65~150</b>	°C

<sup>\*500</sup>mW in the range of Ta =  $-40^{\circ}$ C ~65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C should be applied until 300mW.

#### **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V <sub>cc</sub>	2~6	V
Input Voltage	V <sub>IN</sub>	0~V <sub>cc</sub>	V
Output Voltage	V <sub>OUT</sub>	0~V <sub>cc</sub>	٧
Operating Temperature	T <sub>opr</sub>	<b>−40~85</b>	°C
Input Rise and Fall Time	t <sub>r</sub> , t <sub>f</sub>	$0 \sim 1000 (V_{CC} = 2.0V)$ $0 \sim 500 (V_{CC} = 4.5V)$ $0 \sim 400 (V_{CC} = 6.0V)$	ns

#### DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST	TEST CONDITION		Ta = 25°C			Ta = -4	UNIT										
PANAIVIETEN	STIVIBUL	TEST CONDITION		V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	OINIT									
High - Level Input Voltage	VIH				1.50 3.15 4.20		_ _ _	1.50 3.15 4.20	_ _ _	<									
Low - Level Input Voltage	VIL			2.0 4.5 6.0	_ _ _	_ _ _	0.50 1.35 1.80	_ _ _	0.50 1.35 1.80	V									
High - Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -20\mu A$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	_ _ _	1.9 4.4 5.9	_ _ _	\ \									
Output Voltage		VIH OI VIL	$I_{OH} = -4 \text{ mA}$ $I_{OH} = -5.2 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	_	4.13 5.63	_										
Low - Level Output Voltage	V <sub>OL</sub>	V <sub>OI</sub>	V <sub>OL</sub>	V <sub>OL</sub>	V <sub>OL</sub>	V <sub>OL</sub>	V <sub>OL</sub>	V <sub>OL</sub>	V <sub>OL</sub>	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 20 \mu A$	2.0 4.5 6.0	1 1 1	0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
Output Voltage		VIH OF VIL	$I_{OL} = 4  mA$ $I_{OL} = 5.2  mA$	4.5 6.0	_	0.17 0.18	0.26 0.26	_	0.33 0.33										
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = V_{CC}$ or GND		6.0	_	_	±0.1	_	± 1.0										
Quiescent Supply Current	I <sub>cc</sub>	$V_{1N} = V_{C}$	<sub>C</sub> or GND	6.0			4.0		40.0	$\mu$ A									

# TIMING REQUIREMENTS (Input $t_r = t_f = 6ns$ )

DADAMETED	CYMAROL	BOL TEST CONDITION		Ta =	25°C	Ta = −40~85°C	UNIT
PARAMETER	SYMBOL	1E31 CONDITION	$V_{CC}(V)$	TYP.	LIMIT	LIMIT	UNIT
Minimum Pulse Width	t <sub>W(L)</sub>		2.0 4.5 6.0		75 15 13	95 19 16	
Minimum Pulse Width (CLEAR)	t <sub>W(L)</sub>		2.0 4.5 6.0	_ _ _	75 15 13	95 19 16	
Minimum Set—up Time (DATA)	t <sub>s</sub>		2.0 4.5 6.0		50 10 9	60 12 11	ns
Minimum Set—up Time (A, B, C)	t <sub>s</sub>		2.0 4.5 6.0		25 5 5	30 6 5	
Minimum Set—up Time (DATA)	t <sub>h</sub>		2.0 4.5 6.0	_ _ _	25 5 5	30 6 5	
Minimum Hold Time (A, B, C)	t <sub>h</sub>		2.0 4.5 6.0	_ _ _	0 0 0	0 0 0	

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 15pF$ , $V_{CC} = 5V$ , $Ta = 25^{\circ}C$ , Input $t_r = t_f = 6ns$ )

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t <sub>TLH</sub> t <sub>THL</sub>		_	4	8	
Propagation Delay Time (DATA-Q)	t <sub>pLH</sub> t <sub>pHL</sub>		_	15	22	
Propagation Delay Time (A, B, C-Q)	t <sub>pLH</sub> t <sub>pHL</sub>		_	21	32	ns
Propagation Delay Time $(\overline{G} - Q)$	t <sub>pLH</sub> t <sub>pHL</sub>		_	16	28	
Propagation Delay Time (CLEAR—Q)	t <sub>pHL</sub>		_	13	23	

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50pF$ , Input $t_r = t_f = 6ns$ )

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -4	UNIT	
PARAIVIETER	STIVIBOL	TEST CONDITION	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Output Transition Time	t <sub>TLH</sub> t <sub>THL</sub>		2.0 4.5 6.0		30 8 7	75 15 13	_ _ _	95 19 16	
Propagation Delay Time (DATA-Q)	t <sub>pLH</sub> t <sub>pHL</sub>		2.0 4.5 6.0		56 18 15	130 26 22	_ _ _	165 33 28	
Propagation Delay Time (A, B, C — Q)	t <sub>pLH</sub>		2.0 4.5 6.0	_ _ _	83 25 21	185 37 31	_ _ _	230 46 39	ns
Propagation Delay Time $(\overline{G}-Q)$	t <sub>pLH</sub> t <sub>pHL</sub>		2.0 4.5 6.0	_ _ _	67 20 17	165 33 28	_ _ _	205 41 35	
Propagation Delay Time (CLEAR-Q)	t <sub>pHL</sub>		2.0 4.5 6.0		52 16 14	135 27 23	_ _ _	170 34 29	
Input Capacitance	C <sub>IN</sub>			_	5	10	_	10	, r
Power Dissipation Capacitance	C <sub>PD</sub> (1)			ı	35	_	_	_	pF

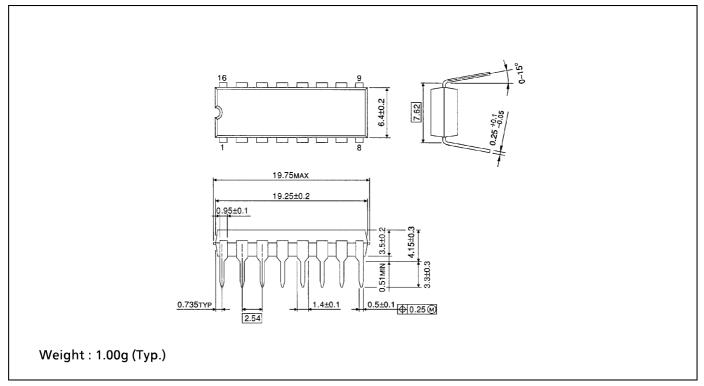
Note (1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}$$
 (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

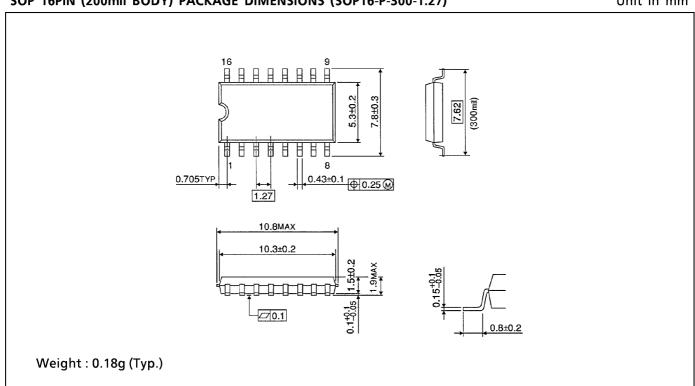
# DIP 16PIN PACKAGE DIMENSIONS (DIP16-P-300-2.54A)

Unit in mm



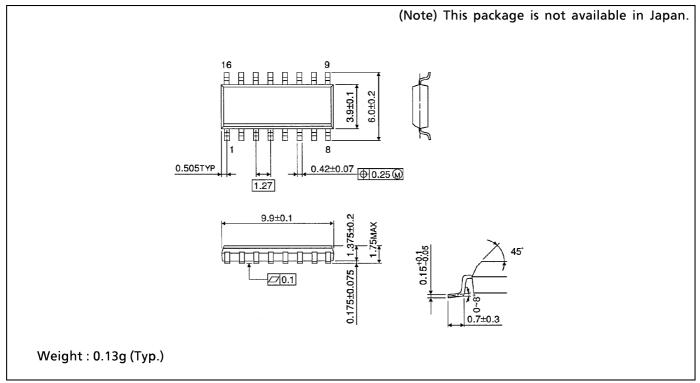
## SOP 16PIN (200mil BODY) PACKAGE DIMENSIONS (SOP16-P-300-1.27)

Unit in mm



# SOP 16PIN (150mil BODY) PACKAGE DIMENSIONS (SOL16-P-150 -1.27)

Unit in mm



7

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